

N-Channel MOSFET

General description

SOT-23 Plastic-Encapsulate Mosfet

FEATURES

- Lead free product is acquired
- Surface mount package
- DC/DC Converter

3

GATE
 SOURCE
 DRAIN

SOT-23



Equivalent Circuit

MECHANICAL DATA

- SOT-23 Small Outline Plastic Package
- Epoxy UL: 94V-0
- Mounting Position: Any

Marking:S4

Maximum Ratings & Thermal Characteristics T_A = 25°C unless otherwise noted

Parameters	Symbol	Value	Unit	
Drain-Source Voltage	VDS	30	V	
Gate-Source Voltage	VGS	±20	V	
Continuous Drain Current	ID	3.3	A	
Pulsed Drain Current	IDM	15		
Continuous Source-Drain Diode Current	IS	0.9		
Power Dissipation	PD	350	mW	
Junction Temperature	Tj	150	°C	
Storage Temperature	Tstg	-50-+150	°C	
Thermal Resistance From Junction to Ambient	RθJA	357	°C/W	

DN2304



Electrical Characteristics T_A = 25°C unless otherwise noted

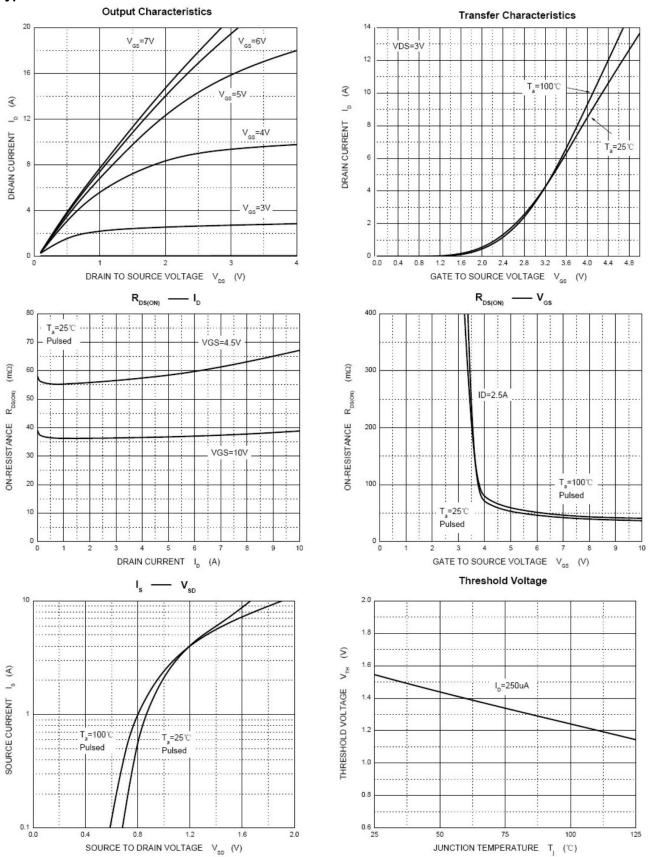
Parameter	Symbols	Test Condition		Limits					
i didiliotoi			Min	Тур	Max	Unit			
Static									
Drain-Source Breakdown Voltage	V(BR)DSS	VGS=0V, ID=250uA	30			V			
Gate-Threshold voltage*	V GS (th)	VDS=VGS, ID=250uA	1	1.55	2.2	V			
Gate-body Leakage	IGSS	VDS=0V, VGS=±20V			±100	nA			
Zero Gate Voltage Drain current	IDSS	VDS=30V, VGS=0V			1	uA			
Drain-Source On-Resistance (a)	RDS(ON)	VGS=10V, ID=3.2A		37	60	mΩ			
		VGS=4.5V, IC=2.8A		57	75				
Forward trans conductance (a)	gfs	VDS=4.5V, ID=2.5A	2.5			S			
Diode forward voltage	VsD	Is=2.7A, VGS=0V		0.8	1.2	V			
Continuous source-drain diode current	Is	Tc=25℃			1.4	Α			
Pulse diode forward current	ISM				15	Α			
Dynamic	•		•						
Input capacitance(b)	Ciss	VDS=15V, VGS=0V,f=1MHz		235		pF			
Output capacitance(b)	Coss			45					
Reverse Transfer capacitance(b)	Crss			17					
Total mate about	Qg	VDS=15V, VGS=10V,ID=3.4A		4.5	6.7				
Total gate charge	Qg	VDS=15V, VGS=4.5V,ID=3.4A		2.1	3.2	nC			
Gate-source charge	Qgs			0.85					
Gate-drain charge	Qgd			0.65					
Gate resistance	Rg	F=1.0MHz	0.8	4.4	8.8	Ω			
Switching (b)									
Turn-on Time	td(on)	VDD=15V, RL=5.6Ω, VGEN=4.5V, ID≈2.7A, RG=1Ω		12	20	- ns			
Rise time	tr			50	75				
Turn-off Time	td(off)			12	20				
Fall time	tf			22	35				
Turn-on Time	td(on)	- VDD=15V, RL=5.6Ω, - VGEN=10V, ID≈2.7A, - RG=1Ω		5	10				
Rise time	tr			12	20				
Turn-off Time	td(off)			10	15				
Fall time	tf			5	10				

Notes:

- a. Pulse Test: Pulse Width ≤300us, Duty Cycle≤2%.b. These parameters have no way to verify.

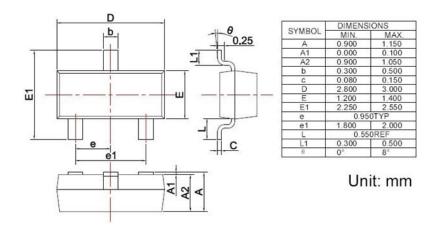


Typical characteristics

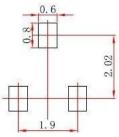




SOT-23 PACKAGE OUTLINE Plastic surface mounted package



Recommended land dimensions for SOT-23 diode. Electrode patterns for PCBs



- Note:
 1.Controlling dimension:in millimeters,
 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only,



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